



CHENMKO ENTERPRISE CO.,LTD

SURFACE MOUNT

CHUMF19PT

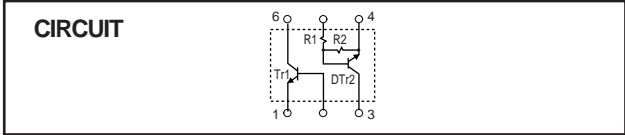
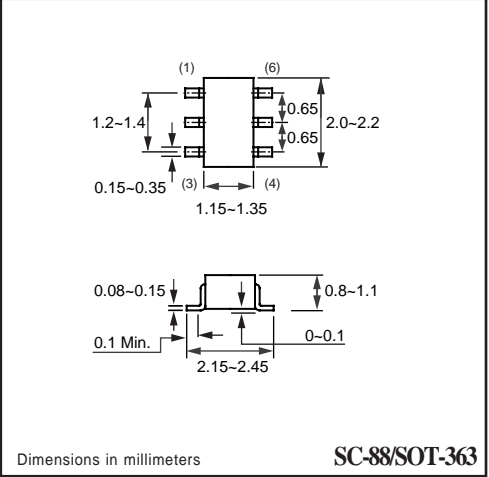
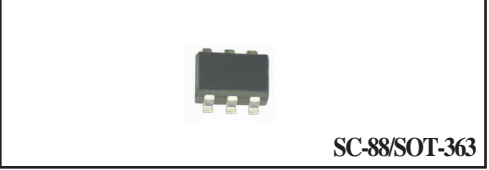
Lead free devices

Power Management (Dual Transistor)

Tr1: VOLTAGE 50 Volts CURRENT 150 mAmpere
 DTr2: VOLTAGE 50 Volts CURRENT 100 mAmpere

APPLICATION
 * Power management circuit

FEATURE
 * Small surface mounting type. (SC-88/SOT-363)
 * Power switching circuit in a single package.
 * Mounting cost and area can be cut in half.
 * Both the 2SC4617 & CHDTC123E in one package.
 * Built in bias resistor(R1=2.2kΩ, Typ.)



2SC4617 LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Vcbo	Collector-base voltage		-	60	V
Vceo	Collector-emitter voltage		-	50	V
Vebo	Emitter-base voltage		-	7	V
Ic	DC Output current		-	150	mA
Pc	Total power dissipation	NOTE.1	-	150	mW
Tstg	Storage temperature		-55	+150	°C
Tj	Junction temperature		-	150	°C

Note

1. 120mW per element must not be exceeded.

CHDTC123E LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CC}	Supply voltage		–	50	V
V _{IN}	Input voltage		-10	+20	V
I _O	DC Output current		–	100	mA
I _{C(Max.)}		NOTE.1	–	100	
P _C	Power dissipation	NOTE.2	–	150	mW
T _{STG}	Storage temperature		-55	+150	°C
T _J	Junction temperature		–	150	°C

Note

1. Characteristics of built-in transistor.
2. Each terminal mounter on a recommended land.

2SC4617 CHARACTERISTICST_{amb} = 25 °C unless otherwise specided.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
BV _{CEO}	Collector-emitter breakdown voltage	I _C =50uA	60	–	–	V
BV _{CBO}	Collector-base breakdown voltage	I _C =1mA	50	–	–	V
BV _{EBO}	Emitter-base breakdown voltage	I _E =50uA	7	–	–	V
I _{CBO}	Collector cut-off current	V _{CB} =60V	–	–	100	nA
I _{EBO}	Emitter cut-off current	V _{EB} =7V	–	–	100	nA
h _{FE}	DC current gain	V _{CE} =6V, I _C =1mA	120	–	560	–
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =50mA, I _B =5mA	–	–	0.4	V
C _{ob}	Collector output capacitance	V _{CB} =12V, I _E =0mA, f=1MHZ	–	2	3.5	pF
f _T	Transition frequency	V _{CE} =12V, I _E =-2mA, f=100MHZ	–	180	–	MHz

Note

1. Pulse test: t_p≤300uS; δ≤0.02.

CHDTC123E CHARACTERISTICST_{amb} = 25 °C unless otherwise specided.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{I(off)}	Input off voltage	I _O =100uA; V _{CC} =5.0V	0.5	–	–	V
V _{I(on)}	Input on voltage	I _O =20mA; V _O =0.3V	–	–	3.0	V
V _{O(on)}	Output voltage	I _O =10mA; I _I =0.5mA	–	0.1	0.3	V
I _I	Input current	V _I =5V	–	–	3.8	mA
I _{C(off)}	Output current	V _I =0V; V _{CC} =50V	–	–	0.5	uA
G ₁	DC current gain	I _O =20mA; V _O =5.0V	20	–	–	–
R ₁	Input resistor		–	2.2	–	KΩ
R _{2/R₁}	Resistor ratio		0.8	1.0	1.2	–
f _T	Transition frequency	I _E =-5mA, V _{CE} =10.0V f=100MHz	–	250	–	MHz

Note

- Pulse test: t_p≤300uS; δ≤0.02.

RATING CHARACTERISTIC CURVES (CHUMF19PT)

2SC4617 Typical Electrical Characteristics

Fig.1 Grounded emitter propagation characteristics

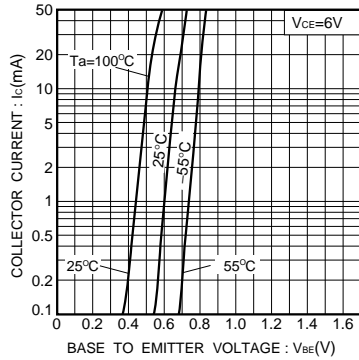


Fig.2 Grounded emitter output characteristics (1)

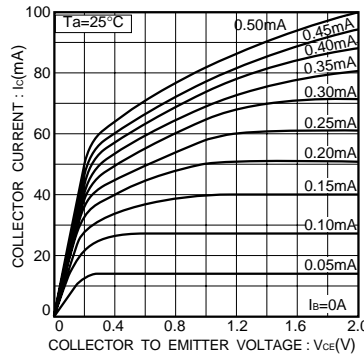


Fig.3 Grounded emitter output characteristics (2)

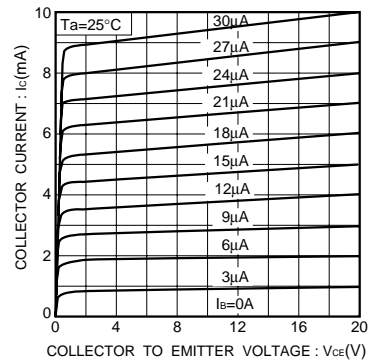


Fig.4 Collector-emitter saturation voltage vs. collector current

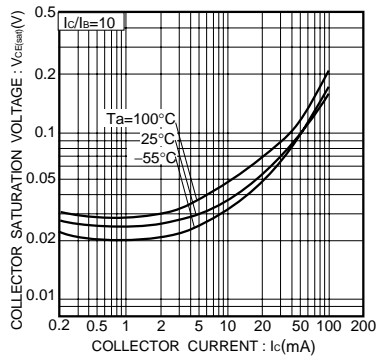


Fig.5 DC current gain vs. collector current

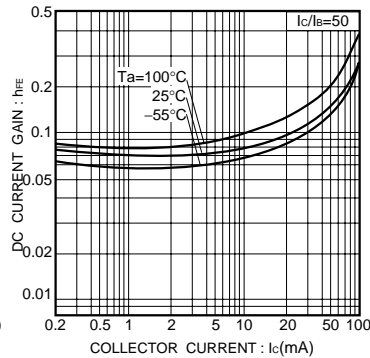
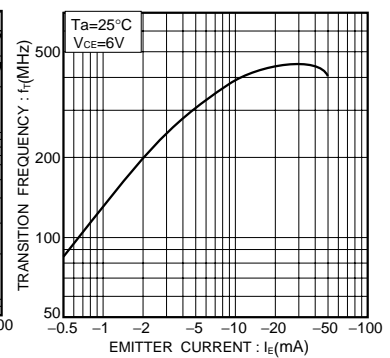


Fig.6 Gain bandwidth product vs. emitter current



RATING CHARACTERISTIC CURVES (CHUMF19PT)

CHDTC123E Typical Electrical Characteristics

Fig.1 Input voltage vs. output current (ON characteristics)

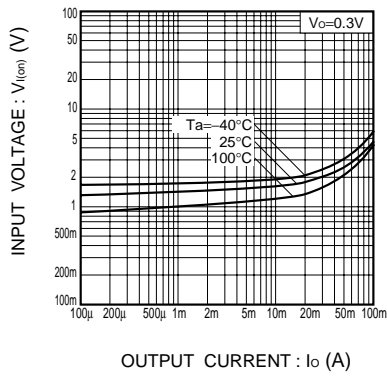


Fig.2 Output current vs. input voltage (OFF characteristics)

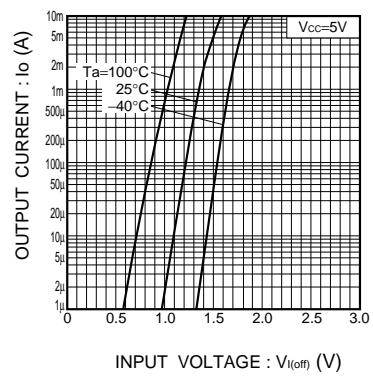


Fig.3 DC current gain vs. output current

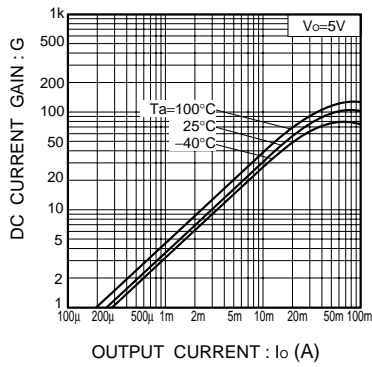


Fig.4 Output voltage vs. output current

